



April 2000

QFET™

# FQPF10N20

## 200V N-Channel MOSFET

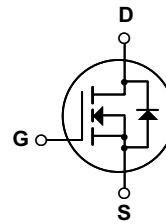
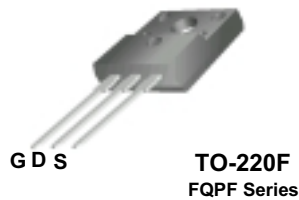
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply, DC-AC converters for uninterrupted power supply, motor control.

### Features

- 6.8A, 200V,  $R_{DS(on)} = 0.36\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 13.5 nC)
- Low Crss ( typical 13 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FQPF10N20	Units
V <sub>DSS</sub>	Drain-Source Voltage	200	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	6.8	A
		4.3	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	27.2	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	180	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	6.8	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	4.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	40	W
		0.32	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	--	3.13	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	200	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	--	0.19	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	--	--	1	μA
		V <sub>DS</sub> = 160 V, T <sub>C</sub> = 125°C	--	--	10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V	--	--	-100	nA

<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.4 A	--	0.28	0.36	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 3.4 A (Note 4)	--	6.7	--	S

<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	--	510	670	pF
C <sub>oss</sub>	Output Capacitance		--	95	130	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	13	17	pF

<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 10 A, R <sub>G</sub> = 25 Ω  (Note 4, 5)	--	13	40	ns
t <sub>r</sub>	Turn-On Rise Time		--	90	190	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	26	70	ns
t <sub>f</sub>	Turn-Off Fall Time		--	50	110	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 160 V, I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V  (Note 4, 5)	--	13.5	18	nC
Q <sub>gs</sub>	Gate-Source Charge		--	3.8	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	5.5	--	nC

<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current	--	--	6.8	A	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current	--	--	27.2	A	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 6.8 A	--	--	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 10 A, di <sub>F</sub> / dt = 100 A/μs (Note 4)	--	130	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	0.6	--	μC

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 5.9mH, I<sub>AS</sub> = 6.8A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 10A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

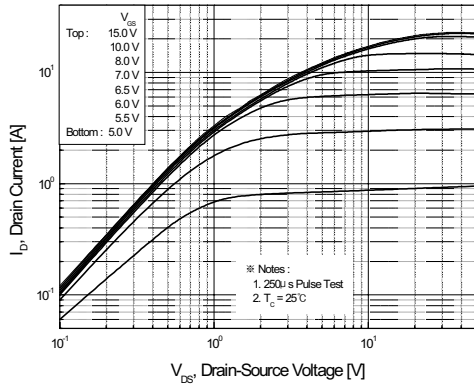


Figure 1. On-Region Characteristics

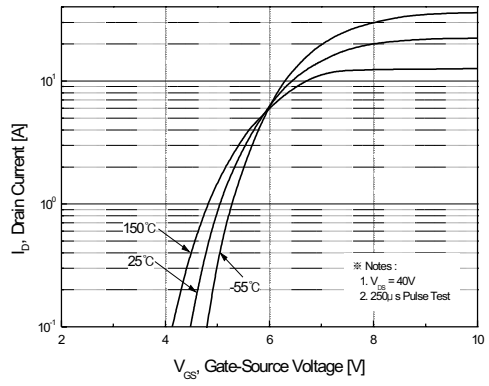


Figure 2. Transfer Characteristics

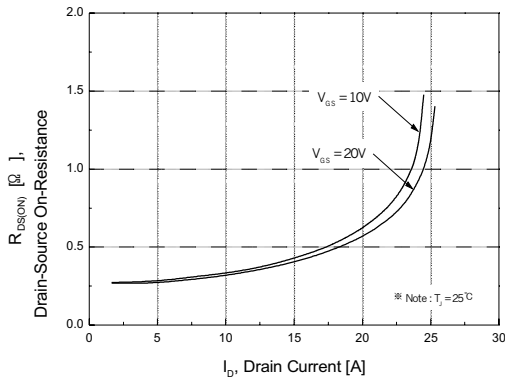


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

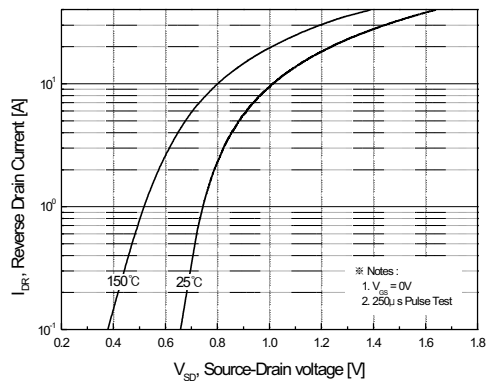


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

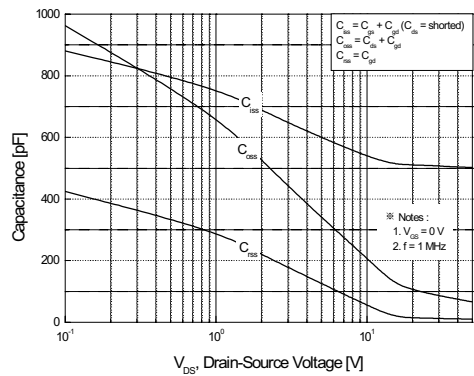


Figure 5. Capacitance Characteristics

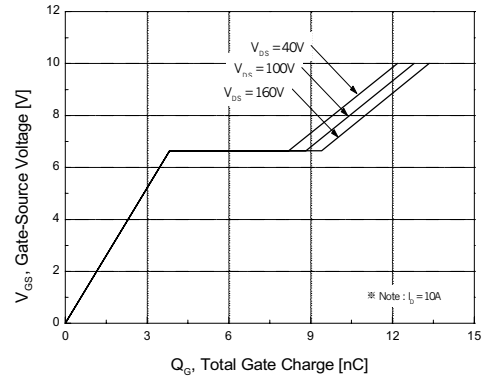
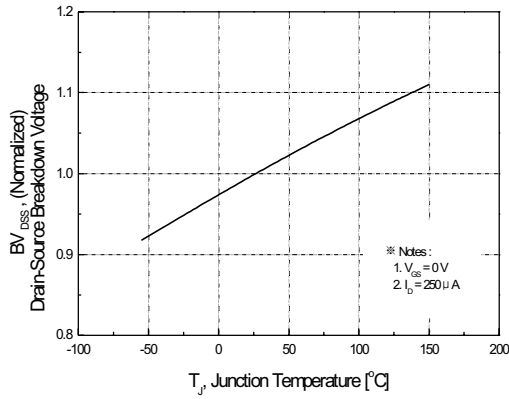
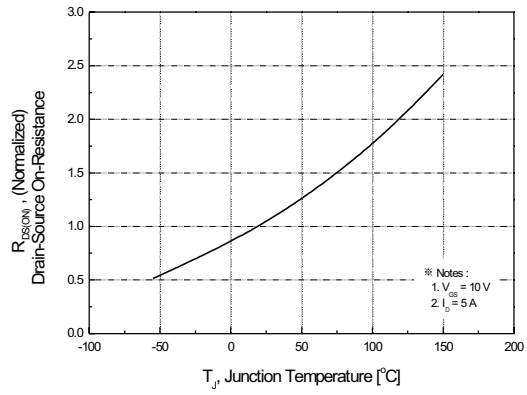


Figure 6. Gate Charge Characteristics

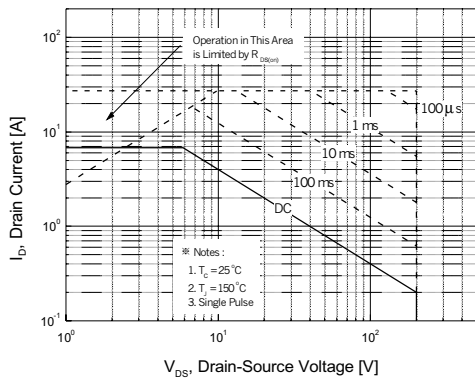
**Typical Characteristics** (Continued)



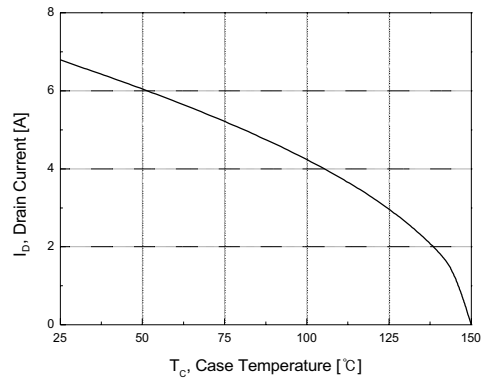
**Figure 7. Breakdown Voltage Variation vs. Temperature**



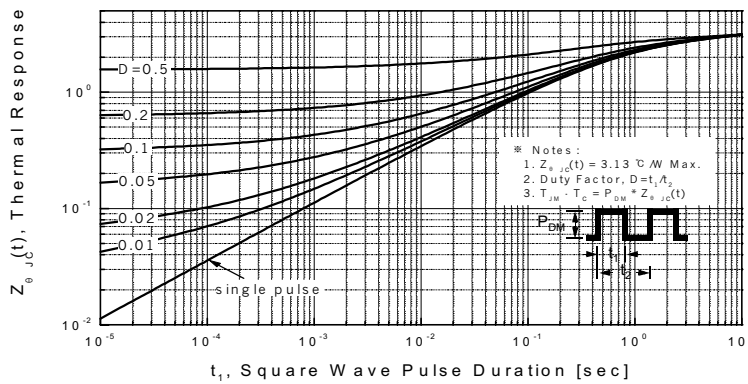
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220F



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